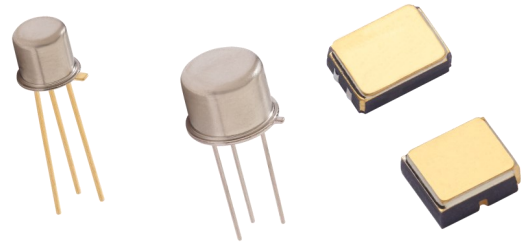


## PNP Silicon Transistor

Rev. V2

### Features

- Available in JAN, JANTX, JANTXV and JANS per MIL-PRF-19500/512
- 2N4029 available in TO-18
- 2N4033 available in TO-39, UA and UB package styles
- Suitable for High Speed Switching and Driver Applications



### Electrical Characteristics

Parameter	Test Conditions	Symbol	Units	Min.	Max.
<b>Off Characteristics</b>					
Collector - Base Cutoff Current	$V_{CB} = -80 \text{ V dc}$	$I_{CBO1}$	$\mu\text{A dc}$	—	-10
Emitter - Base Cutoff Current	$V_{EB} = -5 \text{ V dc}$	$I_{EBO1}$	$\mu\text{A dc}$	—	-10
Collector - Base Cutoff Current	$V_{CB} = -60\text{V dc}$	$I_{CBO2}$	$\text{nA dc}$	—	-10
Collector - Emitter Cutoff Current	$V_{BE} = -2.0 \text{ V dc}; V_{CE} = -60\text{V dc}$	$I_{CEX1}$	$\text{nA dc}$	—	-25
Base - Emitter Cutoff Current	$V_{BE} = -3.0 \text{ V dc}$	$I_{EBO2}$	$\text{nA dc}$	—	-25
Collector-Base Cutoff Current	$T_A = +150^\circ\text{C}$ $V_{CB} = -60 \text{ V dc}$	$I_{CBO3}$	$\mu\text{A dc}$	—	-25
<b>On Characteristics</b>					
Forward Current Transfer Ratio	$V_{CE} = -5.0 \text{ V dc}; I_C = -100 \mu\text{A dc}$ $V_{CE} = -5.0 \text{ V dc}; I_C = -100 \text{ mA dc}$ $V_{CE} = -5.0 \text{ V dc}; I_C = -500 \text{ mA dc}$ $V_{CE} = -5.0 \text{ V dc}; I_C = -1.0 \text{ A dc}$	$h_{FE1}$ $h_{FE2}$ $h_{FE3}$ $h_{FE4}$	-	50 100 70 25	300
Collector - Emitter Saturated Voltage	$I_C = -150 \text{ mA dc}; I_B = -15 \text{ mA dc}$ $I_C = -500 \text{ mA dc}; I_B = -50 \text{ mA dc}$ $I_C = -1.0 \text{ A dc}; I_B = -100 \text{ mA dc}$	$V_{CE(SAT)1}$ $V_{CE(SAT)2}$ $V_{CE(SAT)3}$	$\text{V dc}$	—	-0.15 -0.50 -1.0
Base - Emitter Saturated Voltage	$I_C = -150 \text{ mA dc}; I_B = -15 \text{ mA dc}$ $I_C = -500 \text{ mA dc}; I_B = -50 \text{ mA dc}$	$V_{BE(SAT)1}$ $V_{BE(SAT)2}$	$\text{V dc}$	—	-0.9 -1.2
Forward Current Transfer Ratio	$T_A = -55^\circ\text{C}$ $V_{CE} = -5.0 \text{ V dc}; I_C = -500 \text{ mA dc}$	$h_{FE5}$	-	30	

## PNP Silicon Transistor

Rev. V2

Parameter	Test Conditions	Symbol	Units	Min.	Max.
<b>Dynamic Characteristics</b>					
Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio	$V_{CE} = -10 \text{ V dc}; I_C = -50 \text{ mA dc}; f = 100 \text{ MHz}$	$ h_{FE} $	-	1.5	6.0
Open Circuit Output Capacitance	$V_{CB} = -10 \text{ V dc}; I_E = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	$C_{obo}$	pF	—	20
Input Capacitance (Output Open-Circuited)	$V_{EB} = -0.5 \text{ V dc}; I_C = 0; 100 \text{ kHz} \leq f \leq 1 \text{ MHz}$	$C_{ibo}$	pF	—	80
<b>Pulse Response</b>					
On-Time	$I_C = -500 \text{ mA dc}; I_{B1} = -50 \text{ mA dc}$	$t_d$	ns	—	15
Rise Time	$I_C = -500 \text{ mA dc}; I_{B1} = -50 \text{ mA dc}$	$t_r$	ns	—	25
Storage Time	$I_C = -500 \text{ mA dc}; I_{B1} = -50 \text{ mA dc}$	$t_s$	ns	—	175
Fall Time	$I_C = -500 \text{ mA dc}; I_{B1} = -50 \text{ mA dc}$	$t_f$	ns	—	35

## PNP Silicon Transistor

Rev. V2

### Absolute Maximum Ratings ( $T_A = +25^\circ\text{C}$ unless otherwise specified)

Ratings	Symbol	Value
Collector - Emitter Voltage	$V_{CEO}$	-80 V dc
Collector - Base Voltage	$V_{CBO}$	-80 V dc
Emitter - Base Voltage	$V_{EBO}$	-5.0 V dc
Collector Current	$I_C$	-1.0 A dc
Total Power Dissipation $T_A = +25^\circ\text{C}^{(1)(2)}$ 2N4033 2N4029 2N4033UA 2N4033UB	$P_T$	0.800 W 0.500 W 0.500 W 0.500 W <sup>(4)</sup>
Total Power Dissipation $T_C = +25^\circ\text{C}^{(1)(2)}$ 2N4033 2N4029 2N4033UA 2N4033UB	$P_T$	4 W 1 W N/A N/A
Total Power Dissipation $T_{SP(IS)} = +25^\circ\text{C}^{(1)(2)}$ 2N4033 2N4029 2N4033UA 2N4033UB	$P_T$	N/A N/A 1.5 W 1.5 W
Junction & Storage Temperature Range	$T_J, T_{STG}$	-65°C to +200°C

## PNP Silicon Transistor

Rev. V2

### Absolute Maximum Ratings ( $T_A = +25^\circ\text{C}$ unless otherwise specified)

Ratings	Symbol	Value
Thermal Resistance, Junction to Ambient <sup>(2) (3)</sup> 2N4033 2N4029 2N4033UA 2N4033UB	$R_{\theta JA}$	195 °C/W 325 °C/W 325 °C/W 325 °C/W
Thermal Resistance, Junction to Case <sup>(2) (3)</sup> 2N4033 2N4029 2N4033UA 2N4033UB	$R_{\theta JC}$	40 °C/W 150 °C/W N/A N/A
Thermal Resistance, Junction to Case Kovar <sup>(2) (3)</sup> 2N4033 2N4029 2N4033UA 2N4033UB	$R_{\theta JC}$	35 °C/W N/A N/A N/A
Thermal Resistance, Junction to Solder Pad, Infinite Sink <sup>(2) (3)</sup> 2N4033 2N4029 2N4033UA 2N4033UB	$R_{\theta JSP(IS)}$	N/A N/A 110 °C/W 90 °C/W
Thermal Resistance, Junction to Solder Pad, Ambient <sup>(2) (3)</sup> 2N4033 2N4029 2N4033UA 2N4033UB	$R_{\theta JSP(AM)}$	N/A N/A 40 °C/W N/A

(1) For derating, for encapsulated devices, see figures 7, 8, 9, 10 and 11 of MIL-PRF-19500/512

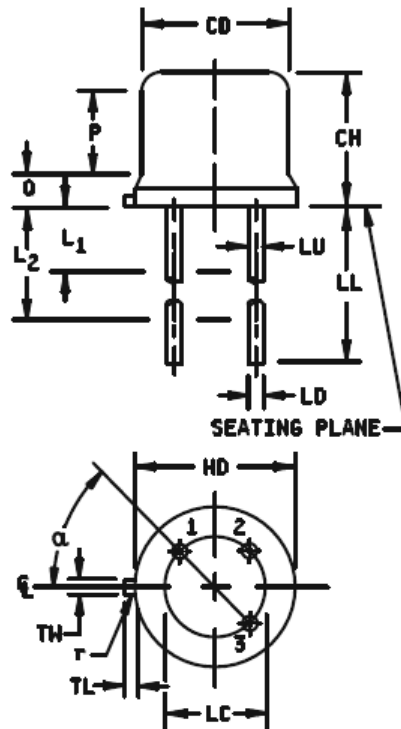
(2) See paragraph 3.3 of MIL-PRF-19500/512

(3) For thermal impedance curves, see figures 12, 13, 13a, 14, 15, 16, 17 and 18 of MIL-PRF-19500/512

(4) For non-thermal conductive PCB or unknown PCB surface mount conditions in free air, substitute figures 8 and 16 for the UB package and use  $R_{\theta JA}$

### Outline Drawing (TO-18)

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.178	.195	4.52	4.95	
CH	.170	.210	4.32	5.33	
HD	.209	.230	5.31	5.84	
LC	.100 TP		2.54 TP		6
LD	.016	.021	0.41	0.53	7, 8
LL	.500	.750	12.70	19.05	7, 8, 12
LU	.016	.019	0.41	0.48	7, 8
L <sub>1</sub>		.050		1.27	7, 8
L <sub>2</sub>	.250		6.35		7, 8
Q		.040		1.02	5
TL	.028	.048	0.71	1.22	3, 4
TW	.036	.046	0.91	1.17	3
R		.010		0.25	10
P	.100		2.54		
$\alpha$	45°TP		45°TP		6



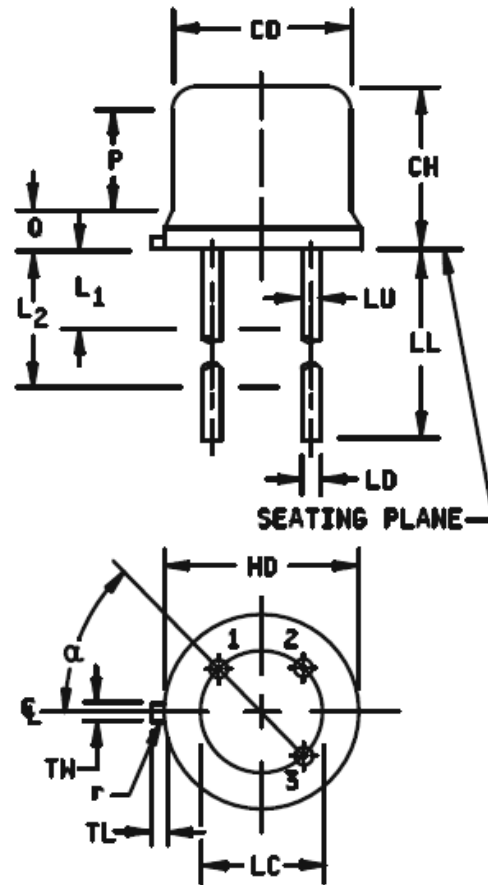
#### NOTES:

1. Dimensions are in inches.
2. Millimeters equivalents are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane .054 +.001 -.000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods.
7. Dimension LU applies between L<sub>1</sub> and L<sub>2</sub>. Dimension LD applies between L<sub>2</sub> and minimum. Diameter is uncontrolled in L<sub>1</sub> and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension r (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi$ x symbology.
12. For "L" suffix devices, dimension LL is 1.50 (38.10 mm) minimum, 1.75 (44.45 mm) maximum.

FIGURE 1. Physical dimensions (type 2N4029) (TO-18).

## Outline Drawing (TO-39)

Symbol	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CD	.305	.335	7.75	8.51	
CH	.240	.260	6.10	6.60	
HD	.335	.370	8.51	9.40	
LC	.200 TP		5.08 TP		6
LD	.016	.021	0.41	0.53	7, 8
LL	.500	.750	12.70	19.05	7, 8, 12
LU	.016	.019	0.41	0.48	7, 8
L <sub>1</sub>		.050		1.27	7, 8
L <sub>2</sub>	.250		6.35		7, 8
Q		.050		1.27	5
TL	.029	.045	0.74	1.14	3, 4
TW	.028	.034	0.71	0.86	3
R		.010		0.25	10
P	.100		2.54		
α	45°TP		45°TP		6

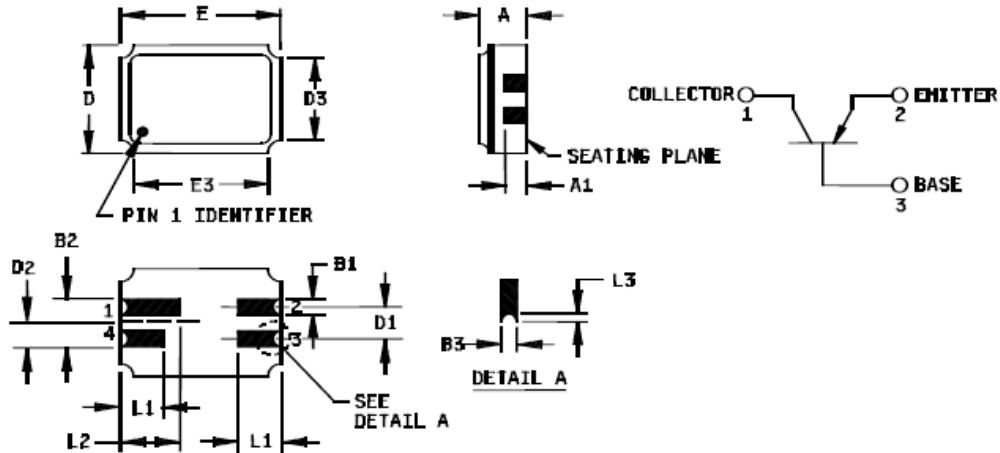


**NOTES:**

1. Dimensions are in inches.
2. Millimeters equivalents are given for general information only.
3. Beyond r (radius) maximum, TW shall be held for a minimum length of .011 (0.28 mm).
4. Dimension TL measured from maximum HD.
5. Body contour optional within zone defined by HD, CD, and Q.
6. Leads at gauge plane .054 +.001 - .000 inch (1.37 +0.03 -0.00 mm) below seating plane shall be within .007 inch (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC. The device may be measured by direct methods.
7. Dimension LU applies between L<sub>1</sub> and L<sub>2</sub>. Dimension LD applies between L<sub>2</sub> and minimum. Diameter is uncontrolled in L<sub>1</sub> and beyond LL minimum.
8. All three leads.
9. The collector shall be internally connected to the case.
10. Dimension r (radius) applies to both inside corners of tab.
11. In accordance with ASME Y14.5M, diameters are equivalent to φx symbology.
12. For "L" suffix devices, dimension LL is 1.50 (38.10 mm) minimum, 1.75 (44.45 mm) maximum.

FIGURE 2. Physical dimensions (type 2N4033) (TO-39).

Outline Drawing (UA Package)



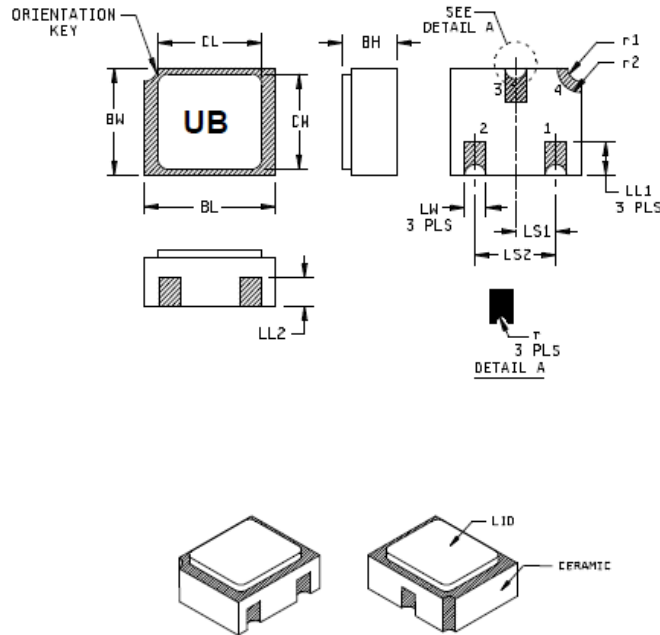
Ltr	Dimensions				Notes	Ltr	Dimensions				Notes
	Inches		Millimeters				Inches		Millimeter		
	Min	Max	Min	Max			Min	Max	Min	Max	
A	.061	.075	1.55	1.91	3	D <sub>2</sub>	.0375 BSC		0.952 BSC		
A <sub>1</sub>	.029	.041	0.74	1.04		D <sub>3</sub>		.155		3.94	
B <sub>1</sub>	.022	.028	0.56	0.71		E	.215	.225	5.46	5.72	
B <sub>2</sub>	.075 REF		1.91 REF			E <sub>3</sub>		.225		5.72	
B <sub>3</sub>	.006	.022	0.15	0.56	5	L <sub>1</sub>	.032	.048	0.81	1.22	
D	.145	.155	3.68	3.9		L <sub>2</sub>	.072	.088	1.83	2.24	
D <sub>1</sub>	.045	.055	1.14	1.39		L <sub>3</sub>	.003		0.08	5	

NOTES:

- Dimensions are in inches.
- Millimeters equivalents are given for general information only.
- Dimension "A" controls the overall package thickness. When a window lid is used, dimension "A" must increase by a minimum of .010 inch (0.254 mm) and a maximum of .040 inch (1.020 mm).
- The corner shape (square, notch, radius, etc.) may vary at the manufacturer's option, from that shown on the drawing.
- Dimensions "B3" minimum and "L3" minimum and the appropriately castellation length define an unobstructed three-dimensional space traversing all of the ceramic layers in which a castellation was designed. (Castellations are required on bottom two layers, optional on top ceramic layer.) Dimension "B3" maximum define the maximum width and depth of the castellation at any point on its surface. Measurement of these dimensions may be made prior to solder dipping.

FIGURE 3. Physical dimensions, surface mount (UA version).

## Outline Drawing (UB Package)



Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
BH	.046	.056	1.17	1.42	
BL	.115	.128	2.92	3.25	
BW	.085	.108	2.16	2.74	
CL		.128		3.25	
CW		.108		2.74	
LL1	.022	.038	0.56	0.97	
LL2	.017	.035	0.43	0.89	

Symbol	Dimensions				Note
	Inches		Millimeters		
	Min	Max	Min	Max	
LS <sub>1</sub>	.036	.040	0.91	1.02	
LS <sub>2</sub>	.071	.079	1.80	2.01	
LW	.016	.024	0.41	0.61	
r		.008		.203	
r1		.012		.305	
r2		.022		.559	

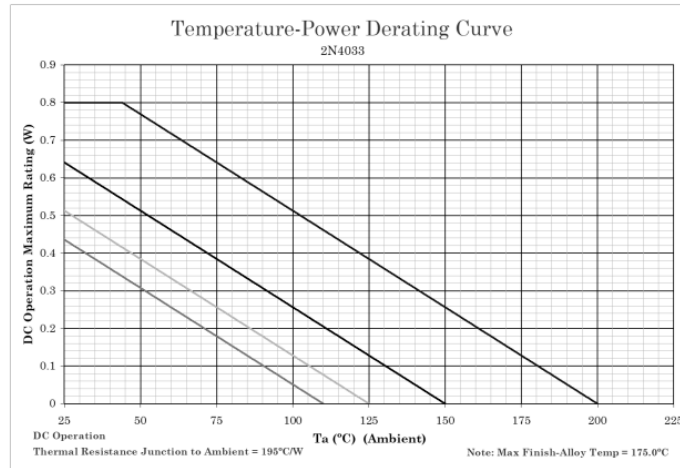
**NOTES:**

1. Dimensions are in inches.
2. Millimeters are given for general information only.
3. Hatched areas on package denote metallized areas
4. Pad 1 = Base, Pad 2 = Emitter, Pad 3 = Collector, Pad 4 = Shielding connected to the lid.
5. In accordance with ASME Y14.5M, diameters are equivalent to  $\phi$ x symbology.

FIGURE 4. Physical dimensions, surface mount (UB version).



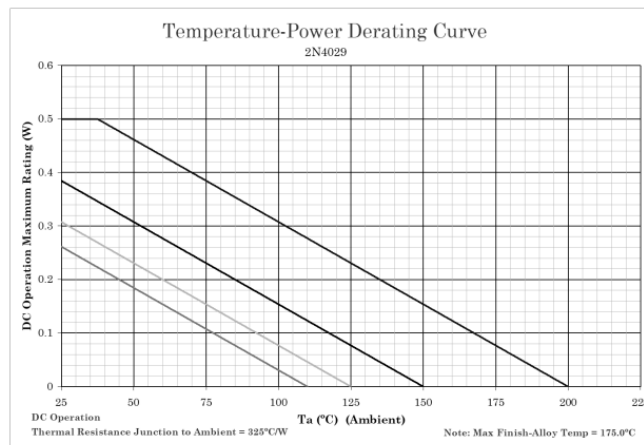
### Temperature-Power Derating Curves



**NOTES:**

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at  $\leq T_J$  specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum  $T_J$  allowed.
2. Derate design curve constrained by the maximum junction temperature ( $T_J \leq 200^\circ\text{C}$ ) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at  $T_J \leq 150^\circ\text{C}$ , where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at  $T_J \leq 125^\circ\text{C}$ , and  $110^\circ\text{C}$  to show power rating where most users want to limit  $T_J$  in their application.

FIGURE 7. Derating for 2N4033 ( $R_{\theta JA}$ ) (TO-39).

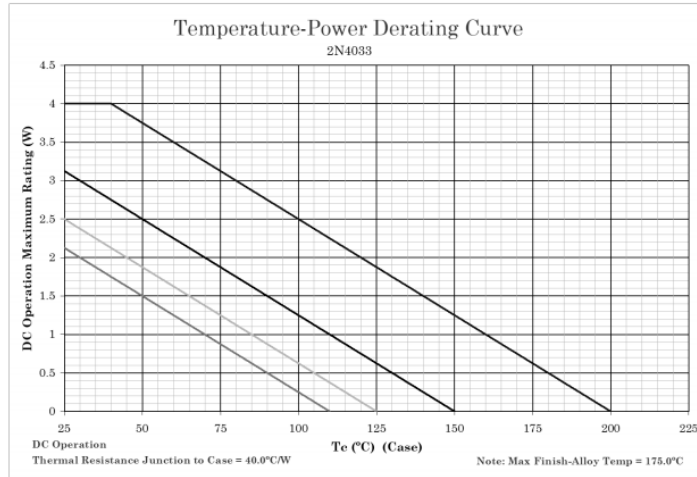


**NOTES:**

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at  $\leq T_J$  specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum  $T_J$  allowed.
2. Derate design curve constrained by the maximum junction temperature ( $T_J \leq 200^\circ\text{C}$ ) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at  $T_J \leq 150^\circ\text{C}$ , where the maximum temperature of electrical test is performed.
4. Derate design curves chosen at  $T_J \leq 125^\circ\text{C}$ , and  $110^\circ\text{C}$  to show power rating where most users want to limit  $T_J$  in their application.

FIGURE 8. Derating for 2N4029 ( $R_{\theta JA}$ ) (TO-18), leads .125 inch (3.17 mm).

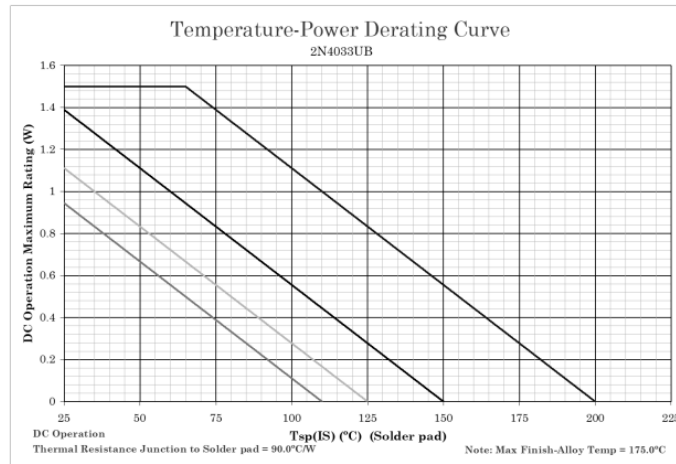
### Temperature-Power Derating Curves



**NOTES:**

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at  $\leq T_J$  specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum  $T_J$  allowed.
2. Derate design curve constrained by the maximum junction temperature ( $T_J \leq 200^\circ\text{C}$ ) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at  $T_J \leq 150^\circ\text{C}$ , where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at  $T_J \leq 125^\circ\text{C}$ , and  $110^\circ\text{C}$  to show power rating where most users want to limit  $T_J$  in their application.

FIGURE 9. Derating for 2N4033 ( $R_{\theta JC}$ ) (TO-39).

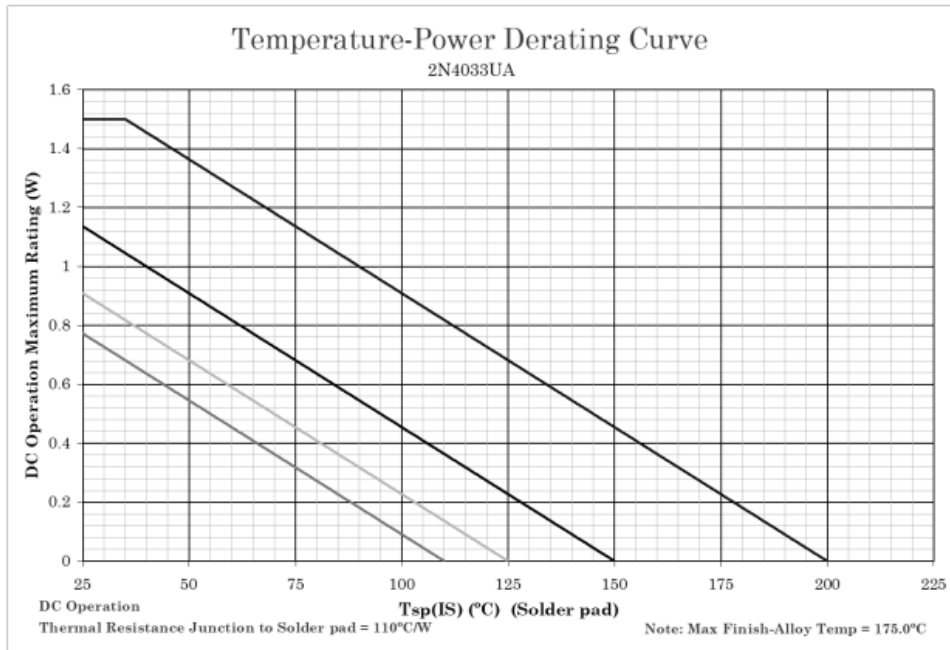


**NOTES:**

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at  $\leq T_J$  specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum  $T_J$  allowed.
2. Derate design curve constrained by the maximum junction temperature ( $T_J \leq 200^\circ\text{C}$ ) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at  $T_J \leq 150^\circ\text{C}$ , where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at  $T_J \leq 125^\circ\text{C}$ , and  $110^\circ\text{C}$  to show power rating where most users want to limit  $T_J$  in their application.

FIGURE 10. Derating for 2N4033UB ( $R_{\theta SP(S)}$ ), infinite sink 3-points.

Temperature-Power Derating Curves



NOTES:

1. This is the true inverse of the worst case thermal resistance value. All devices are capable of operating at  $\leq T_J$  specified on this curve. Any parallel line to this curve will intersect the appropriate power for the desired maximum  $T_J$  allowed.
2. Derate design curve constrained by the maximum junction temperature ( $T_J \leq 200^\circ\text{C}$ ) and power rating specified. (See 1.3 herein.)
3. Derate design curve chosen at  $T_J \leq 150^\circ\text{C}$ , where the maximum temperature of electrical test is performed.
4. Derate design curve chosen at  $T_J \leq 125^\circ\text{C}$ , and  $110^\circ\text{C}$  to show power rating where most users want to limit  $T_J$  in their application.

FIGURE 11. Derating for 2N4033UA ( $R_{\theta JSP(IS)}$ ).

Thermal Impedance Curves

Maximum Thermal Impedance

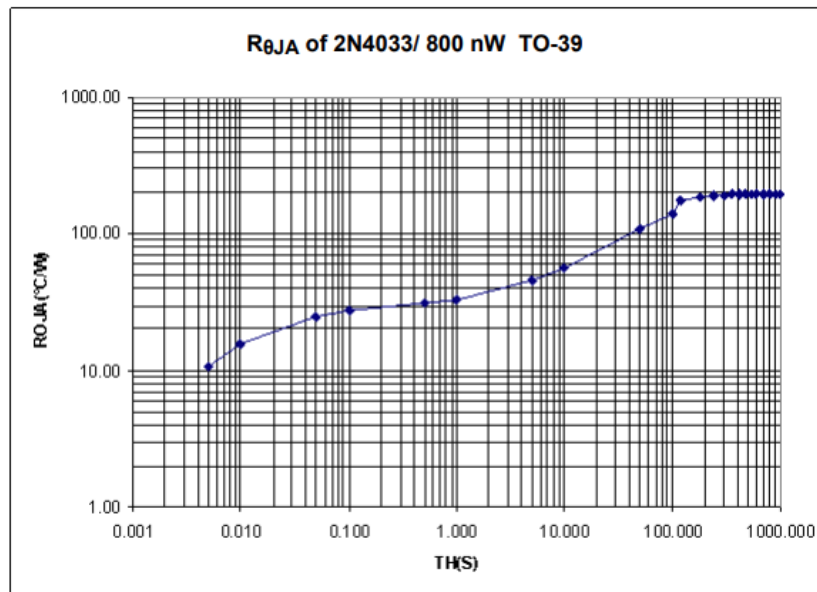


FIGURE 12. Thermal impedance graph (R<sub>θJA</sub>) for 2N4033 (TO-39).

Maximum Thermal Impedance

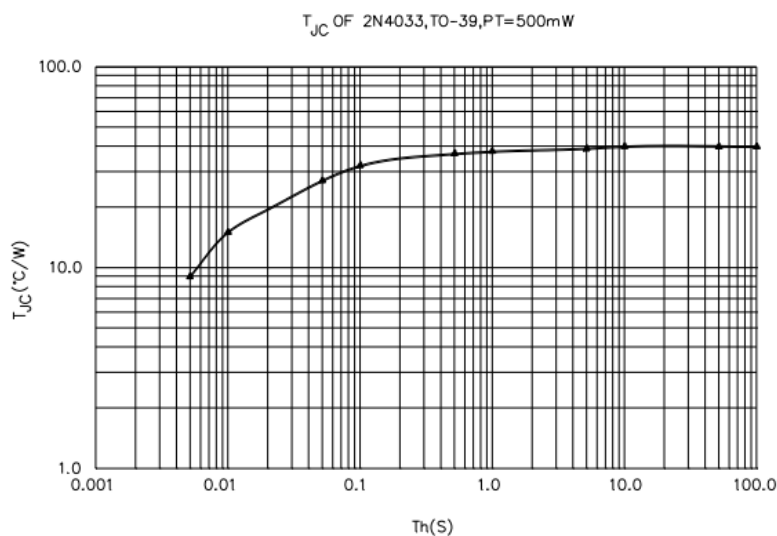
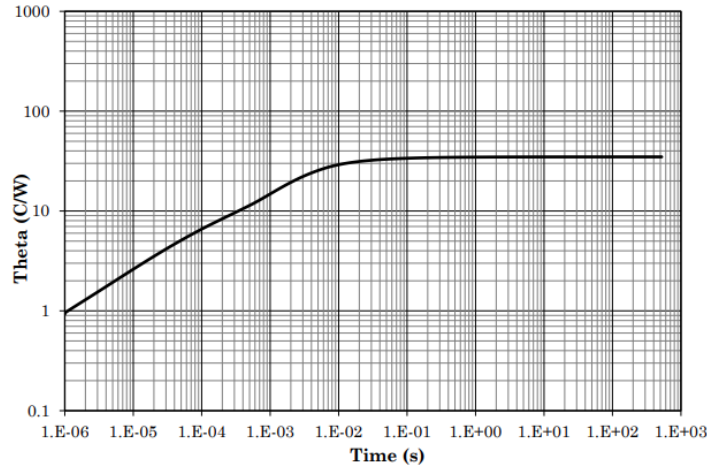


FIGURE 13. Thermal impedance graph (R<sub>θJC</sub>) for 2N4033 (TO-39).

Thermal Impedance Curves

Maximum Thermal Impedance



\* FIGURE 13a. Thermal impedance graph ( $R_{\theta JC}$ ) for Kovar 2N4033 (TO-39).

Maximum Thermal Impedance

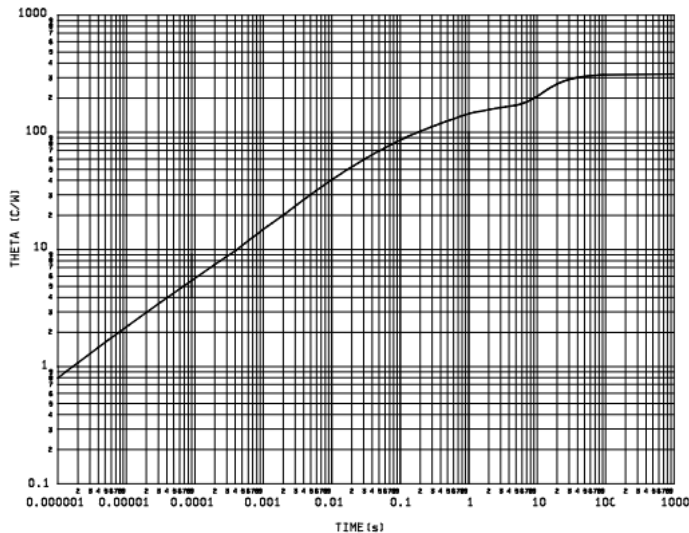


FIGURE 14. Thermal impedance graph ( $R_{\theta JA}$ ) for 2N4029 (TO-18).

### Thermal Impedance Curves

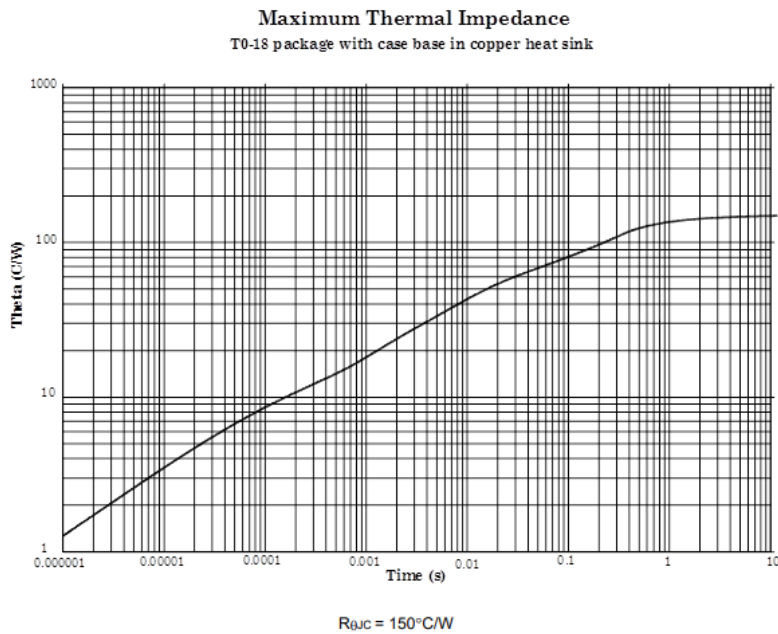


FIGURE 15. Thermal impedance graph ( $R_{\theta JC}$ ) for 2N4029 (TO-18).

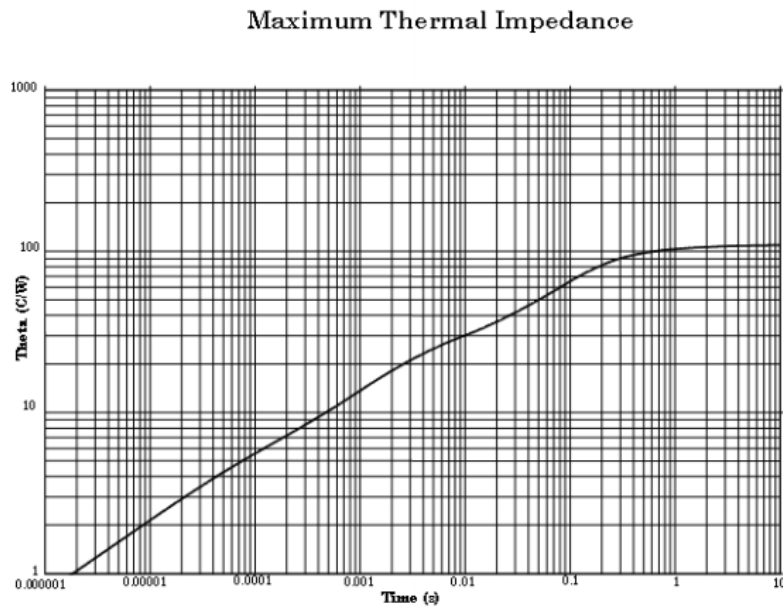
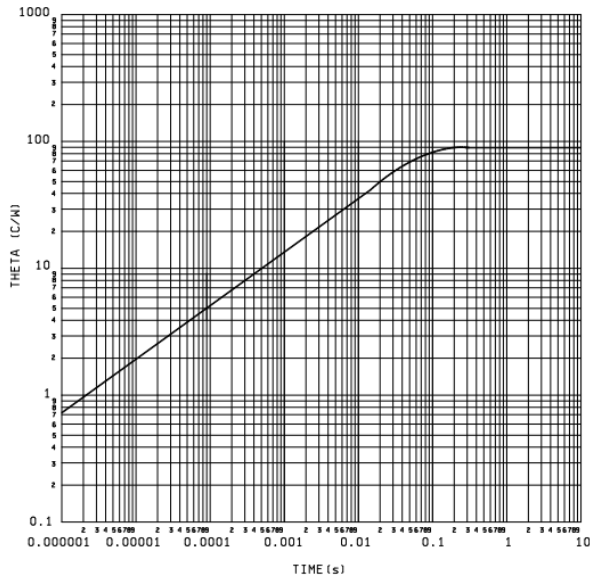


FIGURE 16. Thermal impedance graph ( $R_{\theta JSP(S)}$ ) for 2N4033 (UA).

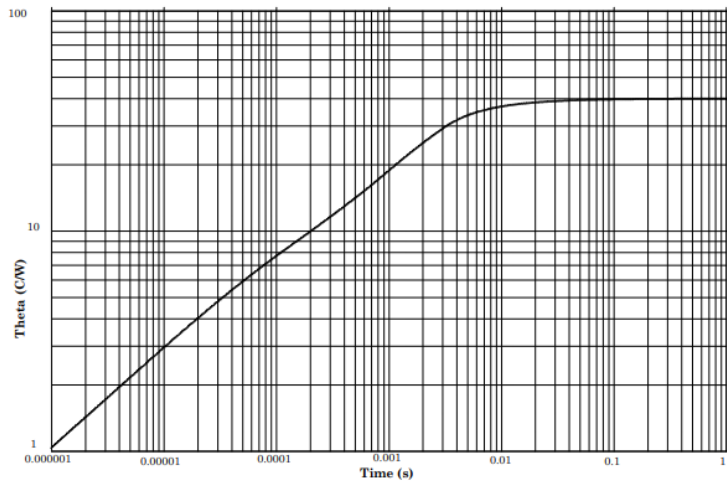
### Thermal Impedance Curves



Ceramic UB package soldered to PCB 3 points solder pad (infinite sink to PCB).  
 $R_{\theta SP(S)} = 90^{\circ}\text{C/W}$

FIGURE 17. Thermal impedance graph ( $R_{\theta SP(S)}$ ) for 2N4029 (UB).

### Maximum Thermal Impedance



2N4033UA 4 point solder pad (adhesive mount to PCB),  $R_{\theta SP(AM)} = 40^{\circ}\text{C/W}$

FIGURE 18. Thermal impedance graph  $R_{\theta SP(AM)}$  for 2N4033UA.

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